

# 2SB1589

## Silicon PNP epitaxial planar type

For low-frequency output amplification

### Features

- Low collector to emitter saturation voltage  $V_{CE(sat)}$ .
- Large collector power dissipation  $P_C$ .
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

### Absolute Maximum Ratings ( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-10	V
Collector to emitter voltage	$V_{CEO}$	-10	V
Emitter to base voltage	$V_{EBO}$	-7	V
Peak collector current	$I_{CP}$	-2	A
Collector current	$I_C$	-1.5	A
Collector power dissipation	$P_C^*$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$

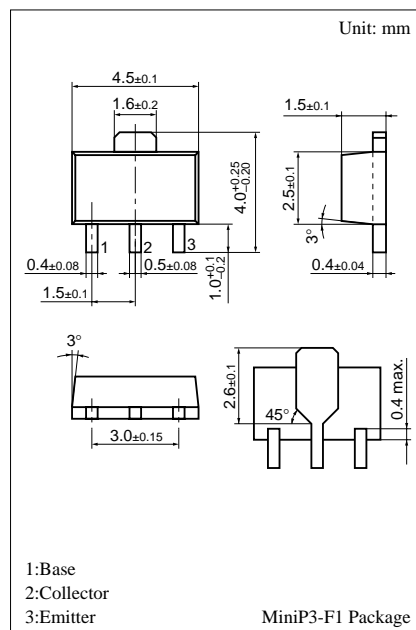
\* Printed circuit board: Copper foil area of  $1\text{cm}^2$  or more, and the board thickness of 1.7mm for the collector portion

### Electrical Characteristics ( $T_a=25^\circ\text{C}$ )

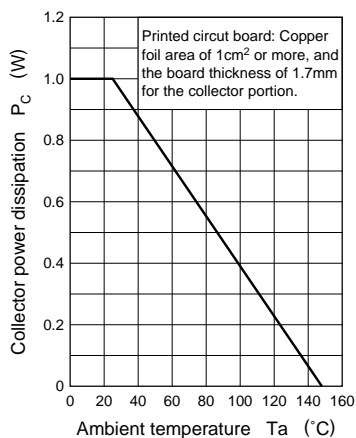
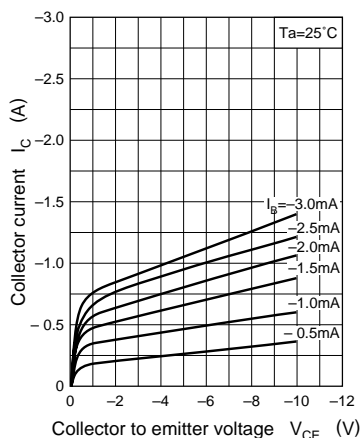
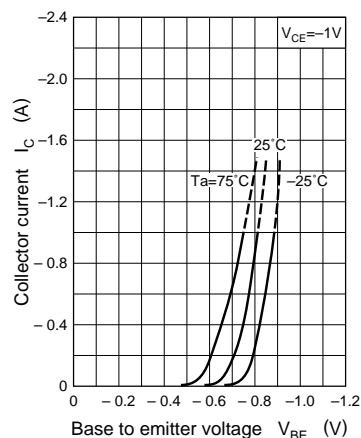
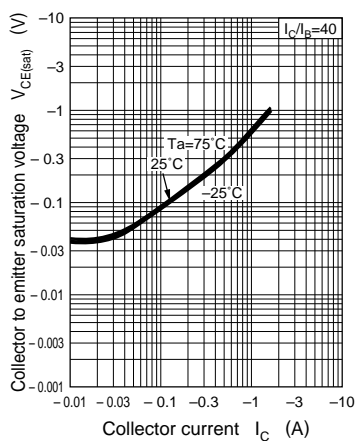
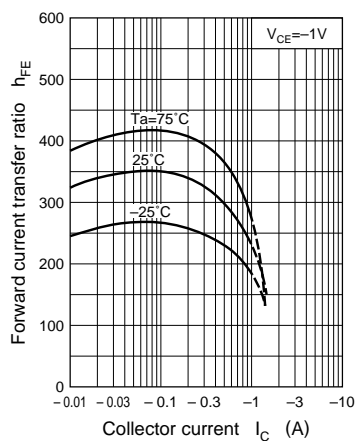
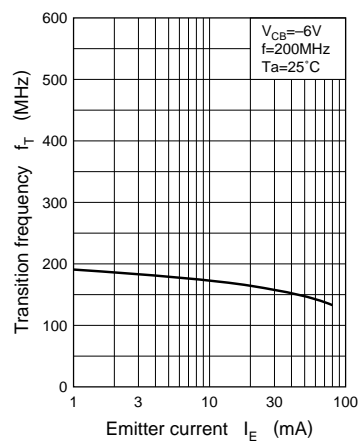
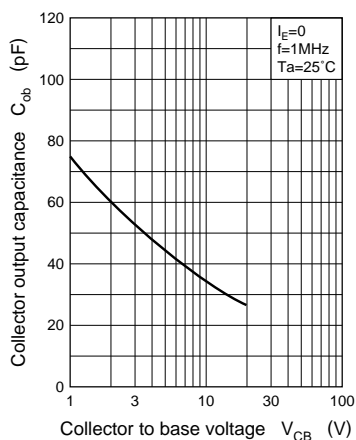
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -7\text{V}$ , $I_E = 0$			-1	$\mu\text{A}$
Collector to base voltage	$V_{CBO}$	$I_C = -10\mu\text{A}$ , $I_E = 0$	-10			V
Collector to emitter voltage	$V_{CEO}$	$I_C = -1\text{mA}$ , $I_B = 0$	-10			V
Emitter to base voltage	$V_{EBO}$	$I_E = -10\mu\text{A}$ , $I_C = 0$	-7			V
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -1\text{V}$ , $I_C = -400\text{mA}^{*2}$	200		700	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1\text{A}$ , $I_B = -25\text{mA}^{*2}$		-0.24	-0.35	V
Transition frequency	$f_T$	$V_{CB} = -6\text{V}$ , $I_E = 50\text{mA}$ , $f = 200\text{MHz}$		190		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$		65		pF
Forward voltage	$V_F^{*1}$	$I_F = -500\text{mA}$			-1.3	V

\*1 Applicable to the built-in diode.

\*2 Pulse measurement



Marking symbol : 1U

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$ 

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